TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSVI)

2SK2989

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : $RDS(ON) = 120 \text{ m}\Omega \text{ (typ.)}$

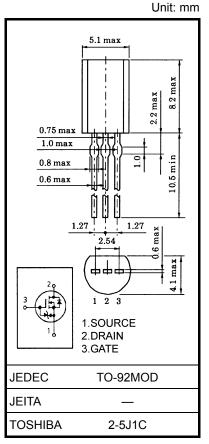
• High forward transfer admittance $|Y_{fs}| = 2.6 \text{ S (typ.)}$

• Low leakage current $:I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 50 \text{ V)}$

• Enhancement-mode : $V_{th} = 1.0 \sim 2.2 \text{ V (VDS} = 10 \text{ V, Ip} = 1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	etics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	50	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	50	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	5	А	
	Pulse (Note 1)	I _{DP}	15	Α	
Drain power dissipation		P _D	0.9	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch-a)}	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.

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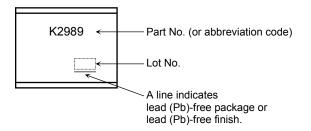
Electrical Characteristics (Ta = 25°C)

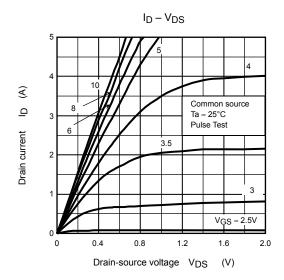
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	irrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 50 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	50	_	_	V
Gate threshold v	oltage/	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.0	_	2.2	V
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = 4 V, I _D = 1.3 A	-	240	330	- mΩ
			V _{GS} = 10 V, I _D = 2.5 A	_	120	150	
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	1.3	2.6	_	S
Input capacitano	e	C _{iss}		_	145	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		25	_	pF
Output capacitance		Coss			75	_	
Switching time	Rise time	t _r	V _{GS} 10V I _D =2.5A V _{OUT}	_	16	_	
	Turn-on time	t _{on}	V_{GS} $0V$	_	23	_	
	Fall time	t _f	V _{DD} =25V	_	27	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \mu s$	_	110	_	
Total gate charg plus gate-drain)	e (gate-source	Qg		ı	6.5	_	
Gate-source charge		Q_{gs}	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$		5	_	nC
Gate-drain ("miller") Charge		Q _{gd}			1.5	_	

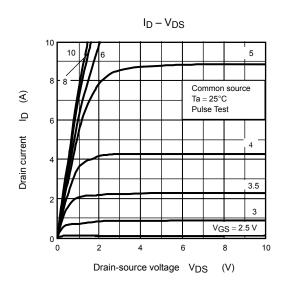
Source-Drain Ratings and Characteristics (Ta = 25°C)

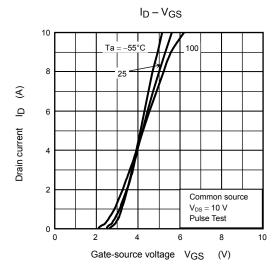
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	5	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	15	Α
Forward voltage (diode)	V_{DSF}	I _{DR} = 5 A, V _{GS} = 0 V	_	_	-1.5	V

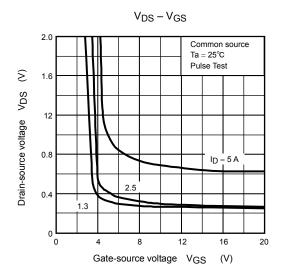
Marking

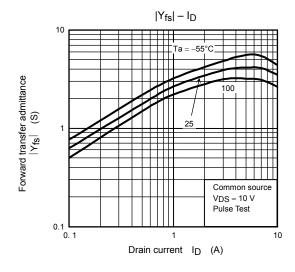


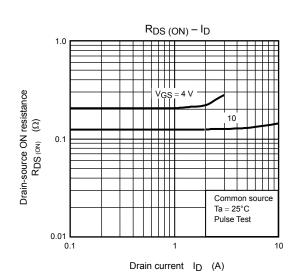


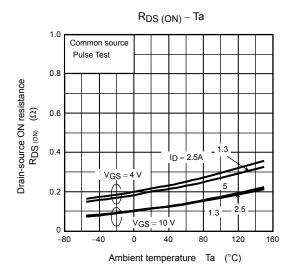


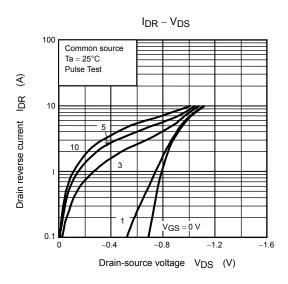


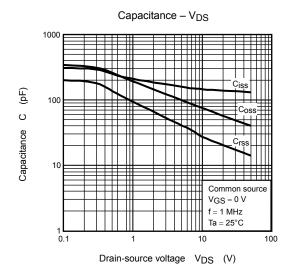


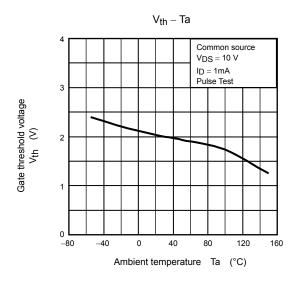


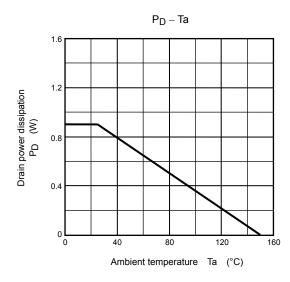


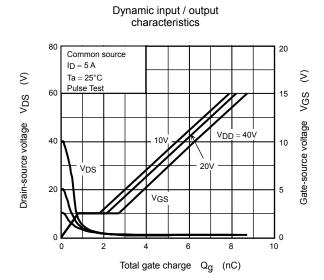


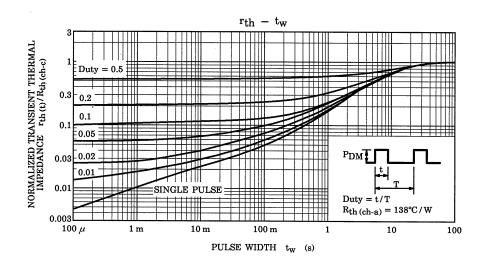


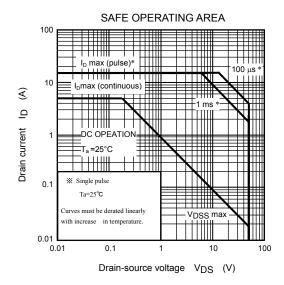












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